REMARKS

Claims 1, 3, 4, 8-10, 12, 16-21 are pending in the present application. Claims 20 and 21 have been amended. Applicants respectfully request examination and allowance of the remaining claims in view of the arguments set forth below.

112 Rejections

Paragraphs 2-3 of the above referenced Office Action state that Claims 20 and 21 are rejected under 35 U.S.C. Section 112 due to uncertainty with respect to the recited limitation "process specific." Applicants have herein amended Claims 20 and 21 to more clearly describe the process specific effect recited being WIW (Within a Wafer) or WID (Within a Die) process effects, as supported in the specification.

103 Rejections

Paragraph 2 of the above referenced office action states that Claims 1-21 are rejected under 35 U.S.C. § 103 as being unpatentable over Cote et al., U.S. Patent No.5,534,106 (hereafter Cote). Applicants respectfully traverse.

Specifically, with respect to Claim 20, Applicants respectfully submit that Cote does not show a "... plurality of regions configured to achieve a specific WIW or WID process effect such that said specific WIW or WID polishing effect can be achieved on said wafer by selectively moving said wafer frictionally one of said plurality of regions, each of said plurality of regions having a respective underlying layer adapted to achieve said specific WIW or

WID process effect." as specifically recited. Applicants respectfully assert that Cote does not show using a respective underlying layer in conjunction with a uniform and homogenous overlying layer forming regions to achieve specific WIW or WID process effects.

With respect to Claim 21, Applicants respectfully submit that Cote does not show "a plurality of regions, each of said plurality of regions configured to achieve a specific WIW or WID effect by using a respective underlying layer in conjunction with the uniform and homogenous overlying layer, wherein the respective underlying layer of each of said plurality of regions is adapted to achieve said specific WIW or WID effect" as claimed.

Further, Applicants respectfully assert that claimed limitations describing the first and second underlying layers "having differing amounts of thickness" to achieve the specific polishing effect are not shown or suggested by Cote. The different amounts of thickness leads to an uneven polishing surface among the different regions. Applicants respectfully submit that underlying layers having different thickness as claimed is not shown or suggested by Cote. Having layers of different hardness is different from different thickness.

Conclusion

In light of the above amendments and remarks, Applicants respectfully request reconsideration of the rejected Claims. The Examiner is urged to contact Applicants' undersigned representative if the Examiner believes such action would expedite resolution of the present Application.

Please charge any additional fees or apply any credits to our PTO deposit account number: 23-0085.

Respectfully submitted,

WAGNER, MURABITO & HAO

Dated: 1/4/02, 2002

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

20. (Amended) A process specific polishing pad having a plurality of regions configured to achieve specific polishing processes effects when used in a wafer polishing machine, the process specific polishing pad comprising:

a polishing pad having an overlying layer, said overlying layer being uniform and homogenous across a polishing surface of said overlying layer, said polishing surface adapted to frictionally contact a wafer as said wafer is polished in said wafer polishing machine; and

said polishing surface having a plurality of regions, each of said plurality of regions configured to achieve a specific WIW or WID process effect such that said specific WIW or WID [polishing] process effect can be achieved on said wafer by selectively moving said wafer frictionally one of said plurality of regions, each of said plurality of regions having a respective underlying layer adapted to achieve said specific WIW or WID process effect.

21. (Amended) A process specific polishing pad having a plurality of regions configured to implement different polishing hardness on the surface of a wafer, the process specific polishing pad comprising:

a polishing pad having an overlying layer, said overlying layer being uniform and homogenous across a polishing surface of said overlying layer, said polishing surface adapted to frictionally contact a wafer as said wafer is polished in said wafer polishing machine; and

said polishing surface having a plurality of regions, each of said plurality of regions configured to achieve a specific [hardness] WIW or WID effect by using a respective underlying layer in conjunction with the uniform and

homogenous overlying layer, wherein the respective underlying layer of each of said plurality of regions is adapted to achieve said specific [hardness] WIW or WID effect.